

D CUMENT-IDENTIFIER: US 5034957 A
TITLE: Semiconductor laser device

DEPR:

Thus, in the Zn-doping of the p-type cladding layer, the diffusion of the Zn into the active layer, and thereby the threshold current, can be suppressed by setting the carrier concentration in the p-type cladding layer to be less than a half of the maximum value obtainable, which is $2.5 \times 10^{17} \text{ cm}^{-3}$.

CCOR:

372/45

CCXR:

372/46

| | Type | Hit | S a r h Text | DBs | Time Stamp | Comments | Error D finiti n | Error |
|---|------|------|---|-------|---------------------|----------|------------------|-------|
| 1 | BRS | 5915 | diffusion with (suppress\$ or avoid\$) | USPAT | 2002/01/07 11:40 | | | 0 |
| 2 | BRS | 104 | (diffusion with (suppress\$ or avoid\$)) and 372/43-50.ccls. | USPAT | 2002/01/07 15:25 | | | 0 |